



DMN67D8LDW

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
60V	5.0Ω @ V <sub>GS</sub> = 10V	230mA
000	7.5Ω @ V <sub>GS</sub> = 5V	190mA

## Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- Power Management Functions

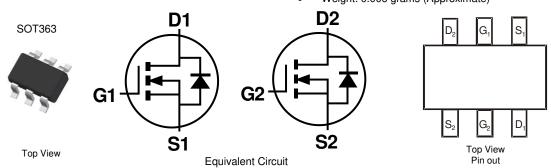
### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe
  (Lead Free Plating). Solderable per MIL-STD-202, Method 208 <sup>(2)</sup>
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8LDW-7	SOT363	3000/Tape & Reel
DMN67D8LDW-13	SOT363	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

$D_2$	$G_1$	S <sub>1</sub>
70	08 YI	M
Μ	Y 80	12
 S <sub>2</sub>	$G_2$	D <sub>1</sub>

7D8 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M = Month (ex: 9 = September)

#### Date Code Key

Notes:

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н	I	J	K	L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±30	V
Continuous Drain Current (Note 6) $V_{GS} = 10V$ State $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			ID	230 180	mA
Maximum Continuous Body Diode Forward Curren	Is	0.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I <sub>DM</sub>	0.8	А

# Thermal Characteristics (@T<sub>A</sub> = $\pm 25^{\circ}$ C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	400	°C/W
Total Power Dissipation (Note 6)		PD	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	312	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			- 71		•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		—	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	IGSS		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0		2.5	V	$V_{DS} = 10V, I_D = 250 \mu A$
Static Drain-Source On-Besistance	Proven		1.5	5.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
	R <sub>DS(ON)</sub>		3.2	7.5	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y <sub>fs</sub>	80	_	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V <sub>SD</sub>		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		22	—	pF	
Output Capacitance	Coss		4.1	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	2.5	—	pF	1 = 1.000112
Gate Resistance	Rg		120	—	Ω	f = 1.0MHz , V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qq	—	361	—	рС	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	—	821	—	рС	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V,
Gate-Source Charge	Q <sub>qs</sub>	_	162	—	рС	I <sub>D</sub> = 250mA
Gate-Drain Charge	Q <sub>gd</sub>		116	—	рС	
Turn-On Delay Time	t <sub>D(ON)</sub>		2.8	—	ns	
Turn-On Rise Time	t <sub>R</sub>		3.0	—	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	7.6	—	ns	$R_L = 150\Omega$ , $V_{GS} = 10V$ , $R_G = 25\Omega$
Turn-Off Fall Time	t <sub>F</sub>		5.6	—	ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

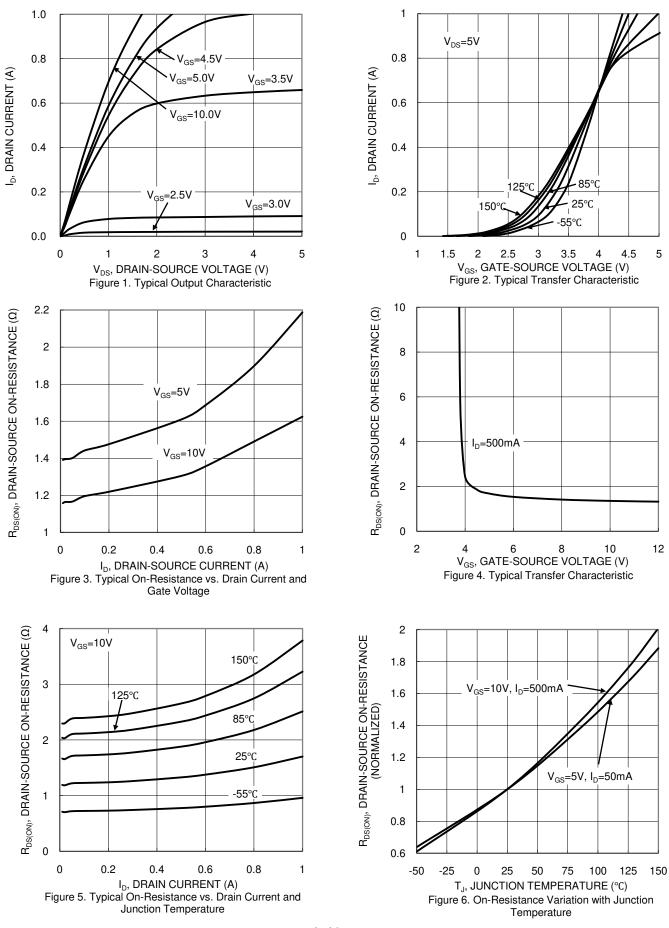
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



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NEW PRODUCT

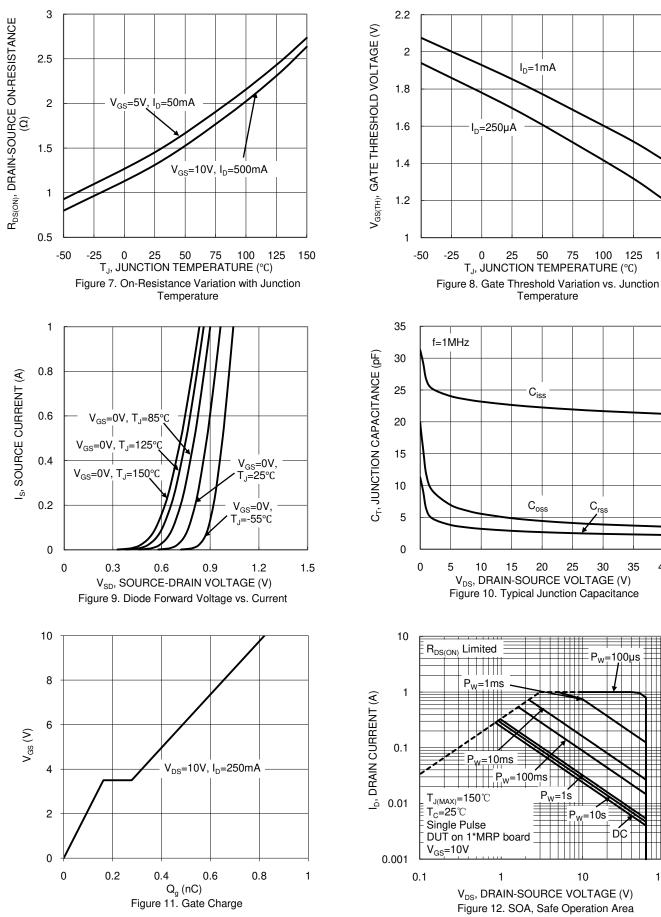
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## DMN67D8LDW

150

40

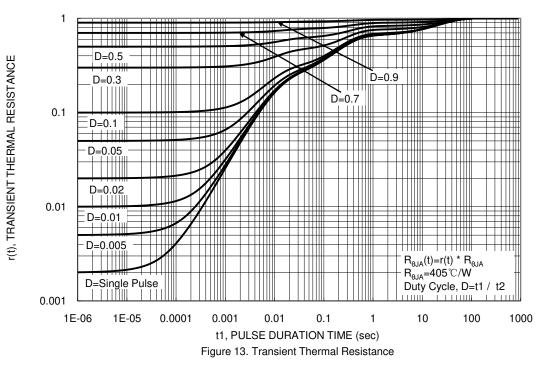


NEW PRODUCT

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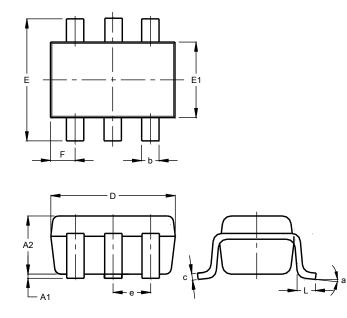
100





## Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

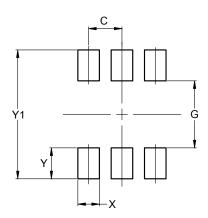


SOT363							
Dim	Min Max Typ						
A1	0.00	0.10	0.05				
A2	0.90	0.90 1.00 1.					
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0	).650 E	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	8°						
All	Dimen	sions	in mm				



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

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